

No.1600A

2SA1318/2SC3331

PNP/NPN Epitaxial Planar Silicon Transistors

AF Amp Applications

Use

. Capable of being used in the low frequency to high frequency range.

Features

. Large current capacity and wide ASO.

(): 2SA1318

Absolute Maximum Ratings at Ta=25°C

			unit
Collector to Base Voltage	V _{CB0}	(-)60	V
Collector to Emitter Voltage	V _{CEO}	(-)50	V
Emitter to Base Voltage	V _{EBO}	(-)6	V
Collector Current	I _C	(-)200	mA
Collector Current (Pulse)	I _{CP}	(-)400	mA
Collector Dissipation	P _C	500	mW
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Electrical Characteristics at Ta=25°C

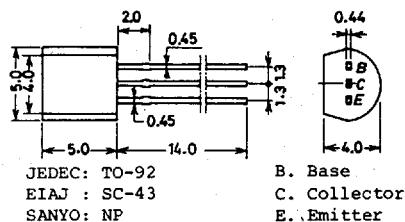
			min	typ	max	unit
Collector Cutoff Current	I _{CBO}	V _{CB} =(-)40V, I _E =0			(-)0.1	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} =(-)5V, I _C =0			(-)0.1	μA
DC Current Gain	h _{FE} (1)	V _{CE} =(-)6V, I _C =(-)1mA	100*		800*	
			(100)		(560)	
	h _{FE} (2)	V _{CE} =(-)6V, I _C =(-)0.1mA		70		
Gain-Bandwidth Product	f _T	V _{CE} =(-)6V, I _C =(-)10mA		200		MHz
Output Capacitance	c _{ob}	V _{CB} =(-)6V, f=1MHz		3.0		pF
				(4.5)		

Continued on next page.

* The 2SA1318/2SC3331 are classified by 1mA h_{FE} as follows:

2SA1318	100 R 200	140 S 280	200 T 400	280 U 560	
2SC3331	100 R 200	140 S 280	200 T 400	280 U 560	400 V 800

Case Outline 2003A
(unit:mm)

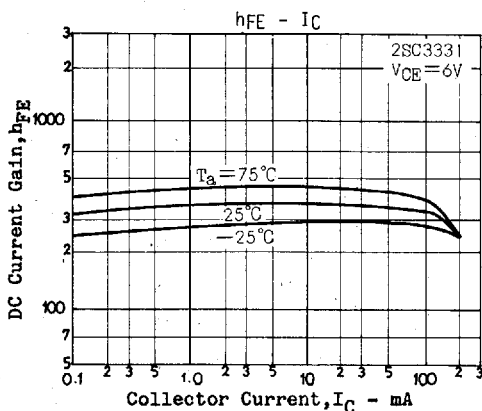
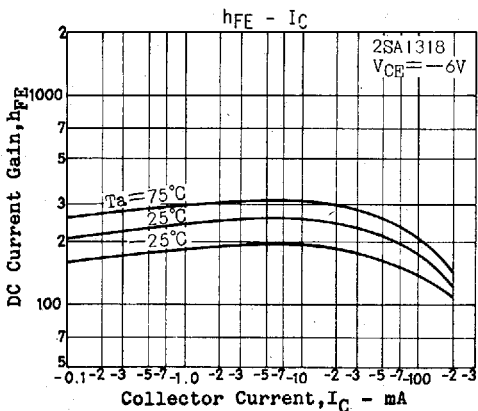
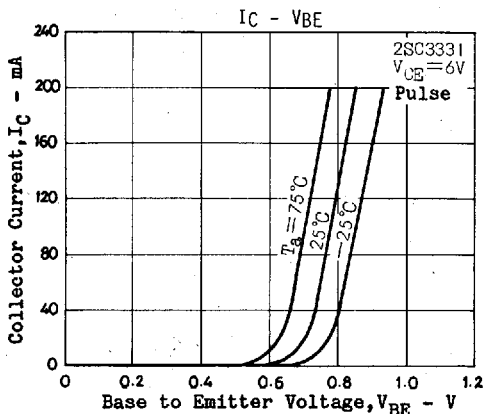
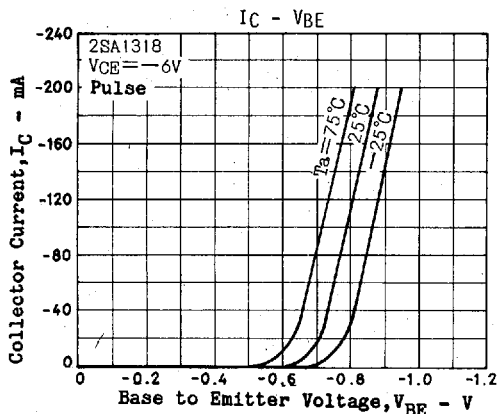
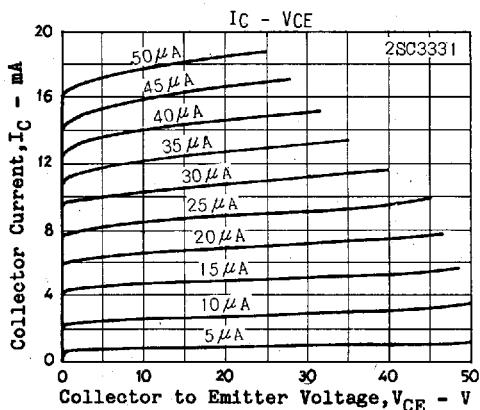
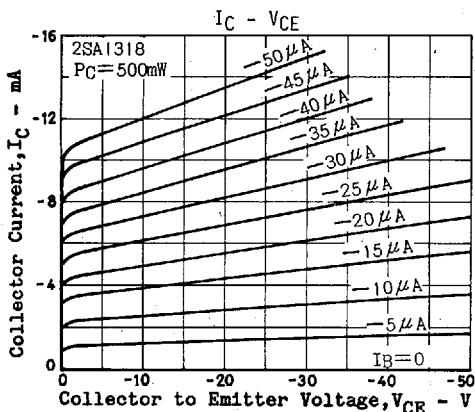


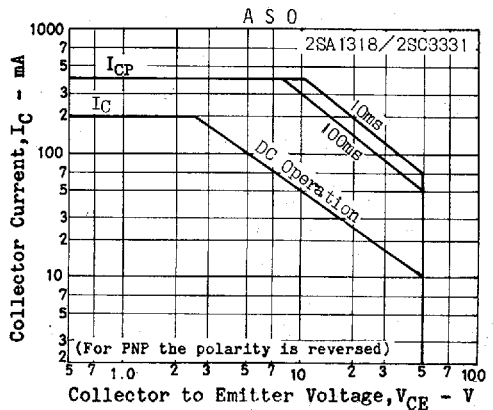
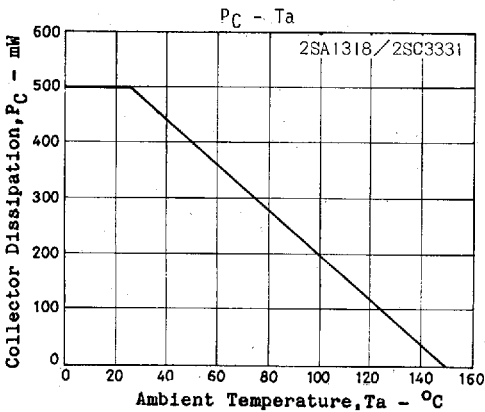
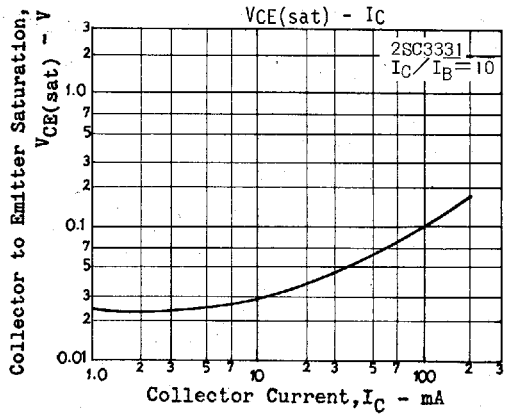
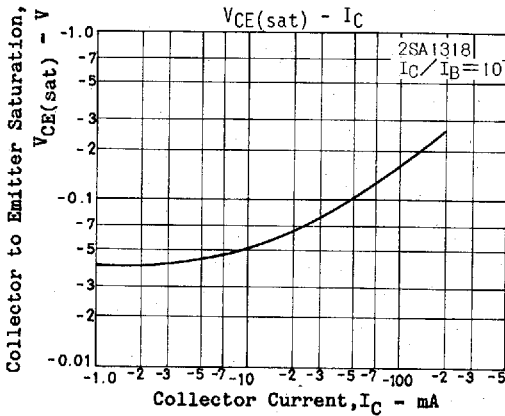
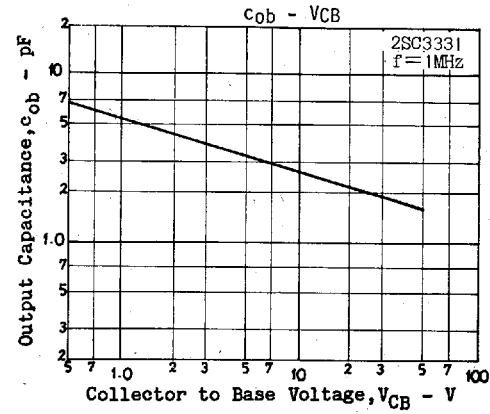
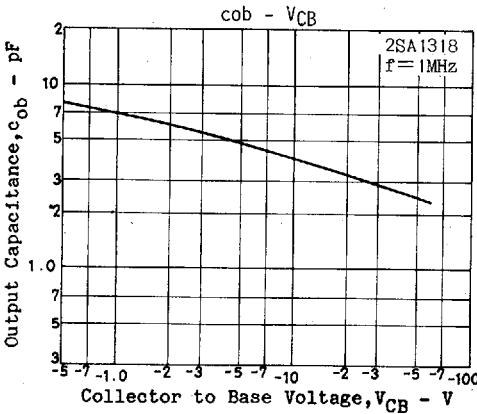
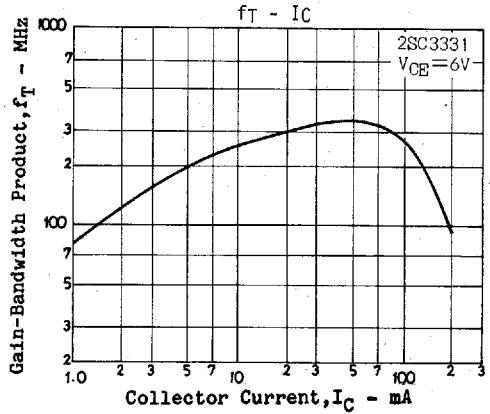
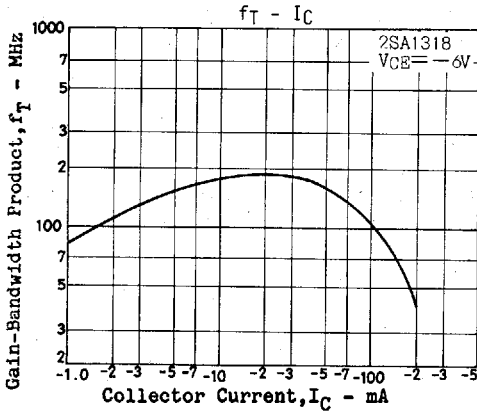
Specifications and information herein are subject to change without notice.

SANYO Electric Co., Ltd. Semiconductor Business Headquarters
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

Continued from preceding page.

		$I_C = (-)100\text{mA}$, $I_B = (-)10\text{mA}$	min	typ	max	unit
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$				(-) 0.3	V
Base to Emitter Saturation Voltage	$V_{BE(sat)}$				(-) 1.0	V
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = (-)10\mu\text{A}, I_E = 0$	(-) 60			V
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = (-)1\text{mA}, R_{BE} = \infty$	(-) 50			V
Emitter to Base Breakdown Voltage	$V_{(BR)EBO}$	$I_E = (-)10\mu\text{A}, I_C = 0$	(-) 6			V

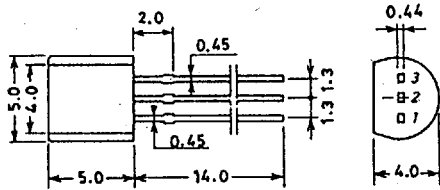




CASE OUTLINES OF LEAD FORMED SMALL SIGNAL TRANSISTORS

- All of Sanyo lead formed small signal transistor case outlines are illustrated below.
- All dimensions are in mm, and dimensions which are not followed by min. or max. are represented by typical values.
- No marking is indicated.

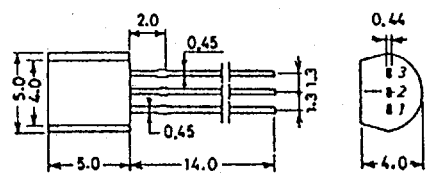
Case Outline 2003A/2003B (unit : mm)



JEDEC : TO-92
EIAJ : SC-43
SANYO : NP

1 : Emitter
2 : Collector
3 : Base

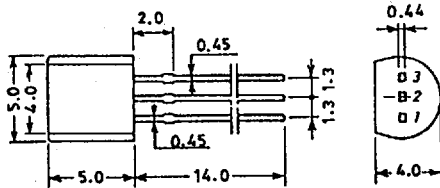
Case Outline 2019A/2019B (unit : mm)



JEDEC : TO-92
EIAJ : SC-43
SANYO : NP

1 : Source
2 : Gate
3 : Drain

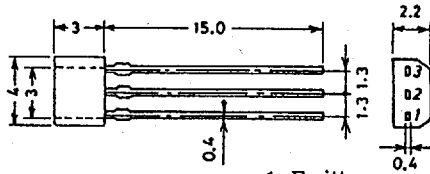
Case Outline 2004A (unit : mm)



JEDEC : TO-92
EIAJ : SC-43
SANYO : NP

1 : Base
2 : Emitter
3 : Collector

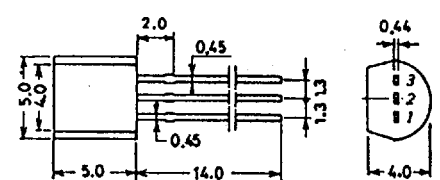
Case Outline 2033 (unit : mm)



1 : Emitter
2 : Collector
3 : Base

SANYO : SPA

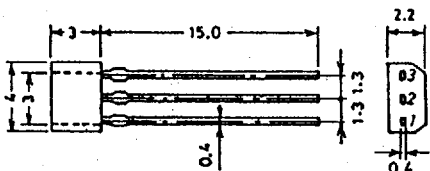
Case Outline 2005A (unit : mm)



JEDEC : TO-92
EIAJ : SC-43
SANYO : NP

1 : Drain
2 : Source
3 : Gate

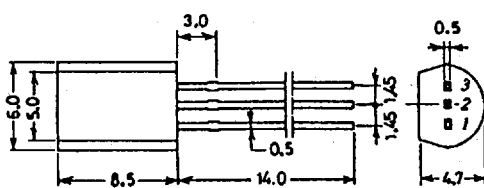
Case Outline 2034/2034A (unit : mm)



1 : Source
2 : Gate
3 : Drain

SANYO : SPA

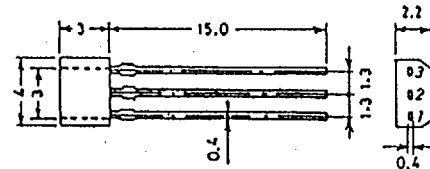
Case Outline 2006A (unit : mm)



EIAJ : SC-51
SANYO : MP

1 : Emitter
2 : Collector
3 : Base

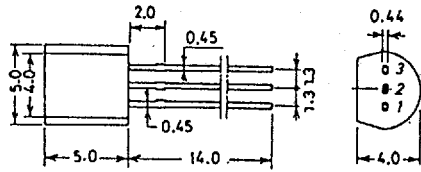
Case Outline 2040 (unit : mm)



1 : Drain
2 : Source
3 : Gate

SANYO : SPA

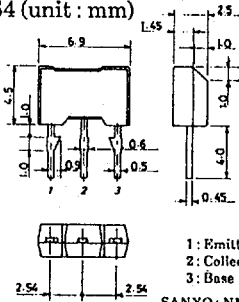
Case Outline 2061 (unit : mm)



JEDEC : TO-92
EIAJ : SC-43
SANYO : NP

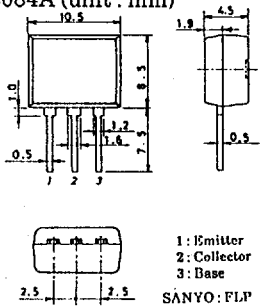
1 : Emitter
2 : Base
3 : Collector

Case Outline 2064 (unit : mm)



1 : Emitter
2 : Collector
3 : Base
SANYO : NMP

Case Outline 2084A (unit : mm)



1 : Emitter
2 : Collector
3 : Base
SANYO : FLP